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最新トランジスタ規格表 (New Transistor Manual) lists all the transistors registered with the Electronic Industries Association of Japan (EIAJ), arranged in a manner easy to look up. We hope that you will make full use of the data provided in this manual by referring to the Japanese-English translation key given below.

型名	社名	用途	構造	最大定格 ($T_b=25^\circ\text{C}$)					電気的特性 ($T_b=25^\circ\text{C}$)										外形	備考	
				V_{ce0} (V)	V_{be0} (V)	I_c (mA)	P_c (mW)	T_j ($^\circ\text{C}$)	I_{c0} 最大値 (μA)	V_{ce} (V)	直流又はパルス I_{cE}		バイアス		h_{FE}	h_{ie}	h_{re}	h_{re}			h_{oe}
1	2	3	4	5					6		7		8				9		10	11	12

- 1 TYPE NUMBER
- 2 ORIGINAL MANUFACTURER
- 3 USES
- 4 MATERIAL AND STRUCTURE
- 5 MAXIMUM RATINGS
- 6 I_{cB0} MAXIMUM VALUE AND V_{cB} VALUE (CRITERIA FOR MEASURING I_{cB0})
- 7 STANDARD VALUE OF DC/PULSE h_{FE} AND V_{cE} , I_c (CRITERIA FOR MEASURING DC/PULSE h_{FE})
- 8 STANDARD VALUE OF h PARAMETERS AND BIAS V_{cB} , I_E (CRITERIA FOR MEASURING h PARAMETERS)

- * INDICATES VALUE IN GROUNDED-BASE OPERATION, OTHERWISE VALUE IN EMITTER-GROUNDED OPERATION.
- 9 $f_{\alpha b}$ OF RF CHARACTERISTIC, EXCEPT IN CASE OF * WHICH INDICATES VALUE OF f_T .
- 10 C_{ob} AND $r_{bb'}$ OF RF CHARACTERISTICS EXCEPT IN CASE OF * IN $r_{bb'}$ COLUMN WHICH INDICATES VALUE OF h_{ie} (real)
- 11 OUTLINE
- 12 REMARKS

: とコンプリ : COMPLEMENTARY TO

型名	社名	用途	構造	最大定格 (T _a = 25°C)					電気的特性 (T _a = 25°C)											外形	備考					
				V _{CEO} (V)	V _{EB0} (V)	I _C (mA)	P _C (mW)	T _J (°C)	I _{CB0} 最大値		直流又はパルス h _{FE}		バイアス		h _{FE} h _{FE} *	h _{ie} h _{ie} * (Ω)	h _{re} h _{re} * (×10 ⁻⁴)	h _{oe} h _{oe} * (μU)	f _β f _β * (Mc)			C _{ob} (pF)	r _{bb'} A _v (real)* (Ω)			
									(μA)	V _{CB} (V)	V _{CE} (V)	I _C (mA)	V _{CB} (V)	I _E (mA)												
2SB721	日立	PA	Si.E	-25	-5	-700	625	150	-0.1	-20	100~320	1	-350	-1	150				350*	20		138D	2SD754 とコンパリ			
" 722	"	"	Si.T	-160	-5	-15A	150W T _c =25°C	150	-1mA	-140	100	-5	-1A									102				
" 723	"	"	"	-200	-5	-15A	150W T _c =25°C	150	-1mA	-160	35~200	-5	-1A									102	2SD753 とコンパリ			
" 724	松下	"	Si.EMe	-60	-5	-3A	25W T _c =25°C	150	-30	-20	80	-3	-1A									268				
" 725	"	AF	Si.EP	-60	-5	-100	250	125	-1	-10	250	-5	-2	-5	1	120	3.4k	1.5	13			138				
" 726	"	"	"	-80	-5	-100	250	125	-0.1	-10	360	-5	-2	-5	1	400	1.6k	1.5	12			138				
" 727	日立	SW	Si.E	-120	-7	-6A	50W T _c =25°C	150	-100	-120	1000~ 20000	-3	-3A		t _{on} = 1 μS, t _{off} = 3 μS							268	ドリフト			
" 728																										
" 729																										
" 730																										
" 731	日電	PA.SW	Si.E	-60	-6	-1A	10W T _c =25°C	150	-0.1	-50	250	-2	-100	-2	10							75*	25	225		
" 732																										
" 733	日電	PA	Si.E	-20	-6	-2A	1W	150	-0.1	-16	360	-2	-100	-2	10							>50*	27	278	2SD773 とコンパリ	
" 734	"	"	"	-60	-6	1A	1W	150	-0.1	-50	250	-2	-100	-2	10							80*	23	278	2SD774 とコンパリ	
" 735																										
" 736	日電	PA	Si.E	-60	-5	-300	200	150	-0.1	-50	200	-1	-50	-6	10							100*	13	176	2SD780 とコンパリ	
" 737	東洋電機	AF.LN	Si.EP	-50	-5	-300	250	125	-0.5	-30	120~560	-6	-10	-6	10	V _{CE} < 150mV I _C = 1mA, R _c = 100Ω, A _v = 80dB						100*	2	138	2SD786 とコンパリ	
" 738	日立	PA	Si.E	-20	-6	-2A	900	150	-2	-16	100~320	-2	-100	-2	10							80*	50	251	2SD787 とコンパリ	
" 739	"	"	"	-20	-6	-2A	900	150	-2	-16	100~320	-2	-100	-2	10							80*	50	251	2SD788 とコンパリ	
" 740	"	"	"	-70	-6	-1A	900	150	-1	-55	100~320	-2	-100	-2	10							65*	35	251	2SD789 とコンパリ	
" 741	"	"	"	-70	-6	-1A	900	150	-1	-55	200	-2	-100	-2	10							65*	35	251	2SD790 とコンパリ	
" 742	日電	"	"	-20	-6	-2A	10W T _c =25°C	150	-0.1	-16	300	-2	-100											225		
" 743	"	PA.SW	"	-40	-5	-3A	10W T _c =25°C	150	-1	-30	100	-5	-1A	-5	100							55*	75	225	2SD793 とコンパリ	
" 744	"	"	"	-70	-5	-3A	10W T _c =25°C	150	-1	-45	100	-5	-500	-5	100							45*	60	225	2SD794 とコンパリ	
" 745	松下	LN	Si.EP	-35	-5	-50	300	135	-0.1	-10	490	-5	-2	-5	1	500	3.5k	1.4	12	NF = 0.5dB (-10V, 1mA, f = 1kHz)				151		
" 746	日立	PA	"	-25	-5	-500	400	150	-0.2	-18	120	-1	-50	-1	50							260*	4.6		C _{oss} 12pS	138
" 747	松下	"	"	-80	-5	-5A	50W T _c =25°C	150	-50	-80	90	-5	-1A											268		
" 748	日立	"	Si.T	-120	-5	-6A	60W T _c =25°C	150	-1mA	-80	100	-5	-1A											332		
" 749	"	"	"	-120	-5	-7A	80W T _c =25°C	150	-1mA	-100	100	-5	-1A											332		
" 750	松下	PA.SW	Si.EP	-60	-5	-2A	35W T _c =25°C	150	-1mA	-60	1000~ 10000	-4	-1A		t _{on} = 0.2 μS, t _{off} = 2 μS									268	ドリフト	